

ABSTRACT

Provided is a method for forming a deposition film,
with which a deposition film having improved uniformity
5 of a film thickness can be formed. The method for
forming a deposition film is a method for forming a
deposition film on a substrate (21) on which a pattern
(22) is formed, and the method includes a deposition step
of placing the substrate (21) on an electrode and
10 applying bias power to the electrode to form a deposition
film (40) on the substrate (21) using plasma obtained by
plasma-processing a deposition gas. A material
constituting the pattern (22) is at least one of a
carbon-containing material, a silicon-containing
15 material, and a metal-containing material. In addition,
the deposition gas contains unsaturated halon. The
unsaturated halon is an unsaturated compound which has a
fluorine atom, a bromine atom, and a carbon atom in a
molecule and has 2 or 3 carbon atoms. Further, a power
20 density of the bias power applied to the electrode is
more than 0 W/cm² and 0.5 W/cm² or less.

Figure 2.